



Rev. 1.4

UTRON

UT62L12816

128K X 16 BIT LOW POWER CMOS SRAM

REVISION HISTORY

REVISION	DESCRIPTION	Released Date
Preliminary Rev. 0.5	1. Original.	Mar, 2001
Rev. 1.0	1. The symbols CE# and OE# and WE# are revised as $\overline{\text{CE}}$ and $\overline{\text{OE}}$ and $\overline{\text{WE}}$. 2. Separate Industrial and Commercial SPEC. 3. Add access time 55ns range.	Jun 21, 2001
Rev. 1.1	1. The extended temperature range is revised. -20 ~80 $\Rightarrow$ -20 ~85	Aug 24, 2001
Rev. 1.2	1. Revised Power supply a、 55ns (max.) for Vcc=2.7V~3.6V b、 70/100ns (max.) for Vcc=2.5V~3.6V 2. Revised block diagram 3. Revised DC ELECTRICAL CHARACTERISTICS : a、 Revised V _{IH} as 2.2V b、 Revised standby current I _{SB1} of LL-version Typical : 3uA $\Rightarrow$ 2uA Maximum : 25uA $\Rightarrow$ 20uA 4. Revised AC ELECTRICAL CHARACTERISTICS : c、 Revised symbol name t _{HZB} as t _{BHZ} d、 Revised symbol name t _{LZB} as t _{BLZ} e、 Revised symbol name t _{PWB} as t _{BW} f、 Revised t _{BLZ} as 10ns (min.) g、 Revised t _{OH} as 10ns (min.) 5. Revised waveforms 6. Revised 48-pin TFBGA package outline dimension : h、 Rev. 1.1 ball diameter=0.3mm i、 Rev. 1.2 ball diameter=0.35mm	Apr 15, 2002
Rev. 1.3	Order information : add 100ns parts	Aug 05, 2002
Rev. 1.4	Add order information for lead free product	May 09, 2003



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FEATURES

- Fast access time :
55ns (max.) for Vcc=2.7V~3.6V
70/100ns (max.) for Vcc=2.5V~3.6V
- CMOS low power operating
Operating current : 45/35/25mA (Icc max.)
Standby current : 20uA (typ.) L-version
2uA (typ.) LL-version
- Single 2.5V~3.6V power supply
- Operating temperature :
Commercial : 0 ~70
Extended : -20 ~85
- All TTL compatible inputs and outputs
- Fully static operation
- Three state outputs
- Data retention voltage : 1.5V (min.)
- Data byte control : $\overline{LB}$ (I/O1~I/O8)
 $\overline{UB}$ (I/O9~I/O16)
- Package : 44-pin 400mil TSOP-
48-pin 6mm × 8mm TFBGA

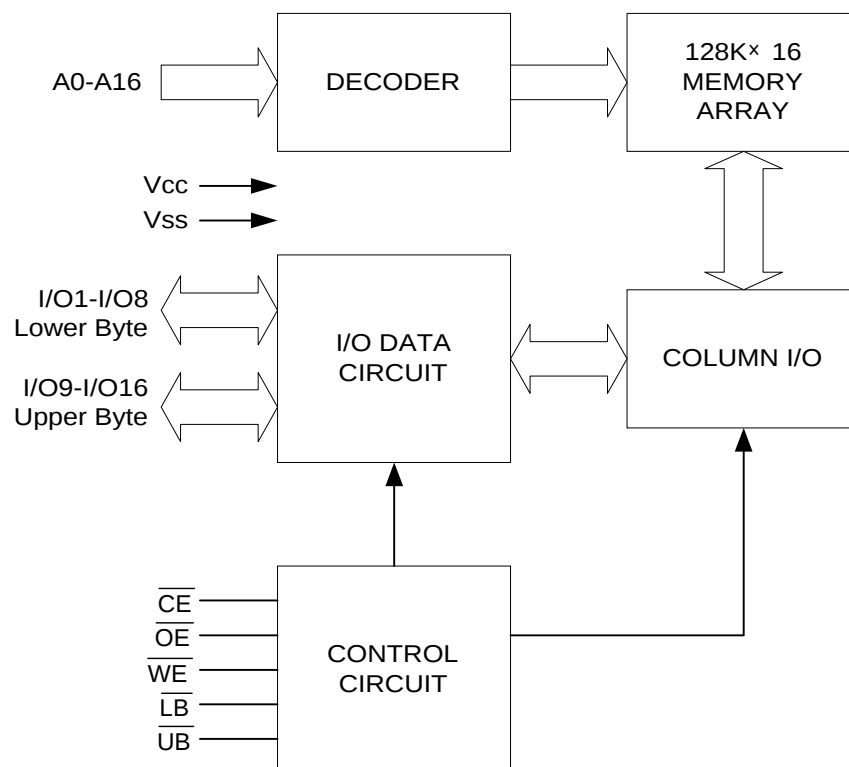
GENERAL DESCRIPTION

The UT62L12816 is a 2,097,152-bit low power CMOS static random access memory organized as 131,072 words by 16 bits.

The UT62L12816 operates from a single 2.5V~3.6V power supply and all inputs and outputs are fully TTL compatible.

The UT62L12816 is designed for low power system applications.

FUNCTIONAL BLOCK DIAGRAM





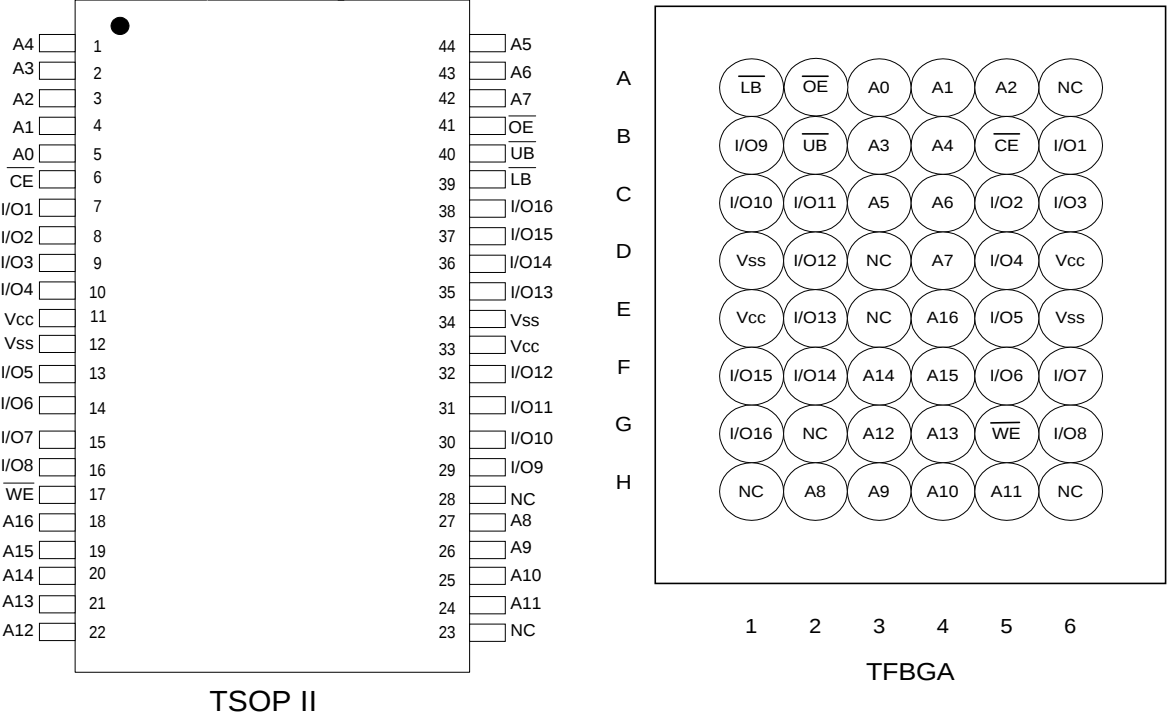
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PIN CONFIGURATION



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 - A16	Address Inputs
I/O1 - I/O16	Data Inputs/Outputs
CE	Chip Enable Input
WE	Write Enable Input
OE	Output Enable Input
LB	Lower Byte Control
UB	Upper Byte Control
V _{CC}	Power Supply
V _{SS}	Ground
NC	No Connection



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TRUTH TABLE

MODE	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	$\overline{LB}$	$\overline{UB}$	I/O OPERATION		SUPPLY CURRENT
						I/O1-I/O8	I/O9-I/O16	
Standby	H	X	X	X	X	High – Z	High – Z	I_{SB}, I_{SB1}
	X	X	X	H	H	High – Z	High – Z	
Output Disable	L	H	H	L	X	High – Z	High – Z	I_{CC}, I_{CC1}, I_{CC2}
	L	H	H	X	L	High – Z	High – Z	
Read	L	L	H	L	H	D _{OUT}	High – Z	I_{CC}, I_{CC1}, I_{CC2}
	L	L	H	H	L	High – Z	D _{OUT}	
	L	L	H	L	L	D _{OUT}	D _{OUT}	
Write	L	X	L	L	H	D _{IN}	High – Z	I_{CC}, I_{CC1}, I_{CC2}
	L	X	L	H	L	High – Z	D _{IN}	
	L	X	L	L	L	D _{IN}	D _{IN}	

Note: H = V_{IH}, L = V_{IL}, X = Don't care.

ABSOLUTE MAXIMUM RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Terminal Voltage with Respect to V _{SS}	V _{TERM}	-0.5 to 4.6	V
Operating Temperature	Commercial	T _A	0 to 70
	Extended	T _A	-20 to 85
Storage Temperature	T _{STG}	-65 to +150	
Power Dissipation	P _D	1	W
DC Output Current	I _{OUT}	50	mA
Soldering Temperature (under 10 secs)	T _{solder}	260	

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

DC ELECTRICAL CHARACTERISTICS (V_{CC} = 2.5V~3.6V, T_A = 0 to 70 / -20 to 85 (E))

PARAMETER	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Power Voltage	V _{CC}		55	2.7	3.0	3.6	V
			70/100	2.5	--	3.6	V
Input High Voltage	V _{IH} ^{*1}			2.2	-	V _{CC} +0.3	V
Input Low Voltage	V _{IL} ^{*2}			-0.2	-	0.6	V
Input Leakage Current	I _{LI}	V _{SS}	V _{IN} V _{CC}	- 1	-	1	μA
Output Leakage Current	I _{LO}	V _{SS}	V _{I/O} V _{CC} ; Output Disable	- 1	-	1	μA
Output High Voltage	V _{OH}	I _{OH} = -1mA		2.2	-	-	V
Output Low Voltage	V _{OL}	I _{OL} = 2.1mA		-	-	0.4	V
Operating Power Supply Current	I _{CC}	Cycle time=min, 100%duty I _{I/O} =0mA, $\overline{CE}$ =V _{IL}	55	-	30	45	mA
			70	-	25	35	mA
			100	-	20	25	mA
Average Operation Current	I _{CC1}	100%duty, I _{I/O} =0mA $\overline{CE}$ 0.2V, other pins at 0.2V or V _{CC} -0.2V	TCycle=1μs	-	4	5	mA
	I _{CC2}		TCycle=500ns	-	8	10	mA
Standby Current (TTL)	I _{SB}	$\overline{CE}$ =V _{IH} , other pins =V _{IL} or V _{IH}		-	0.3	0.5	mA
Standby Current (CMOS)	I _{SB1}	$\overline{CE}$ =V _{CC} -0.2V other pins at 0.2V or V _{CC} -0.2V	-L	-	20	80	μA
			-LL	-	2	20	μA

Notes:

1. Overshoot : V_{CC}+3.0v for pulse width less than 10ns.
2. Undershoot : V_{SS}-3.0v for pulse width less than 10ns.
3. Overshoot and Undershoot are sampled, not 100% tested.



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CAPACITANCE ($T_A=25^\circ\text{C}$, $f=1.0\text{MHz}$)

PARAMETER	SYMBOL	MIN.	MAX	UNIT
Input Capacitance	C_{IN}	-	6	pF
Input/Output Capacitance	$C_{I/O}$	-	8	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Input Pulse Levels	0V to 3.0V
Input Rise and Fall Times	5ns
Input and Output Timing Reference Levels	1.5V
Output Load	$C_L = 30\text{pF}$, $I_{OH}/I_{OL} = -1\text{mA}/2.1\text{mA}$

AC ELECTRICAL CHARACTERISTICS ($T_A=0^\circ\text{C}$ to 70°C / -20°C to 85°C (E))

(1) READ CYCLE

PARAMETER	SYMBOL	UT62L12816-55 $V_{CC}=2.7\text{V}\sim 3.6\text{V}$		UT62L12816-70 $V_{CC}=2.5\text{V}\sim 3.6\text{V}$		UT62L12816-100 $V_{CC}=2.5\text{V}\sim 3.6\text{V}$		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	t_{RC}	55	-	70	-	100	-	ns
Address Access Time	t_{AA}	-	55	-	70	-	100	ns
Chip Enable Access Time	t_{ACE}	-	55	-	70	-	100	ns
Output Enable Access Time	t_{OE}	-	30	-	35	-	50	ns
Chip Enable to Output in Low Z	t_{CLZ}^*	10	-	10	-	10	-	ns
Output Enable to Output in Low Z	t_{OLZ}^*	5	-	5	-	5	-	ns
Chip Disable to Output in High Z	t_{CHZ}^*	-	20	-	25	-	30	ns
Output Disable to Output in High Z	t_{OHZ}^*	-	20	-	25	-	30	ns
Output Hold from Address Change	t_{OH}	10	-	10	-	10	-	ns
$\overline{LB}$, $\overline{UB}$ Access Time	t_{BA}	-	55	-	70	-	100	ns
$\overline{LB}$, $\overline{UB}$ to High-Z Output	t_{BHZ}	-	25	-	30	-	40	ns
$\overline{LB}$, $\overline{UB}$ to Low-Z Output	t_{BLZ}	10	-	10	-	10	-	ns

(2) WRITE CYCLE

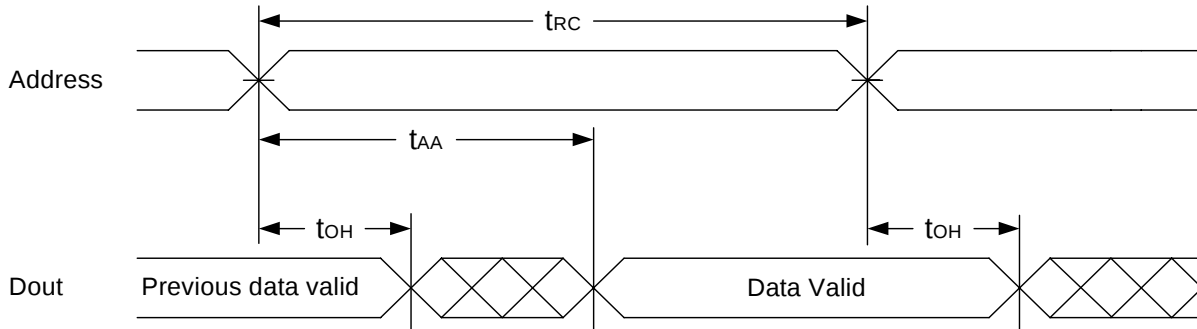
PARAMETER	SYMBOL	UT62L12816-55 $V_{CC}=2.7\text{V}\sim 3.6\text{V}$		UT62L12816-70 $V_{CC}=2.5\text{V}\sim 3.6\text{V}$		UT62L12816-100 $V_{CC}=2.5\text{V}\sim 3.6\text{V}$		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	t_{WC}	55	-	70	-	100	-	ns
Address Valid to End of Write	t_{AW}	50	-	60	-	80	-	ns
Chip Enable to End of Write	t_{CW}	50	-	60	-	80	-	ns
Address Set-up Time	t_{AS}	0	-	0	-	0	-	ns
Write Pulse Width	t_{WP}	45	-	55	-	70	-	ns
Write Recovery Time	t_{WR}	0	-	0	-	0	-	ns
Data to Write Time Overlap	t_{DW}	25	-	30	-	40	-	ns
Data Hold from End of Write Time	t_{DH}	0	-	0	-	0	-	ns
Output Active from End of Write	t_{OW}^*	5	-	5	-	5	-	ns
Write to Output in High Z	t_{WHZ}^*	-	30	-	30	-	40	ns
$\overline{LB}$, $\overline{UB}$ Valid to End of Write	t_{BW}	45	-	60	-	80	-	ns

*These parameters are guaranteed by device characterization, but not production tested.

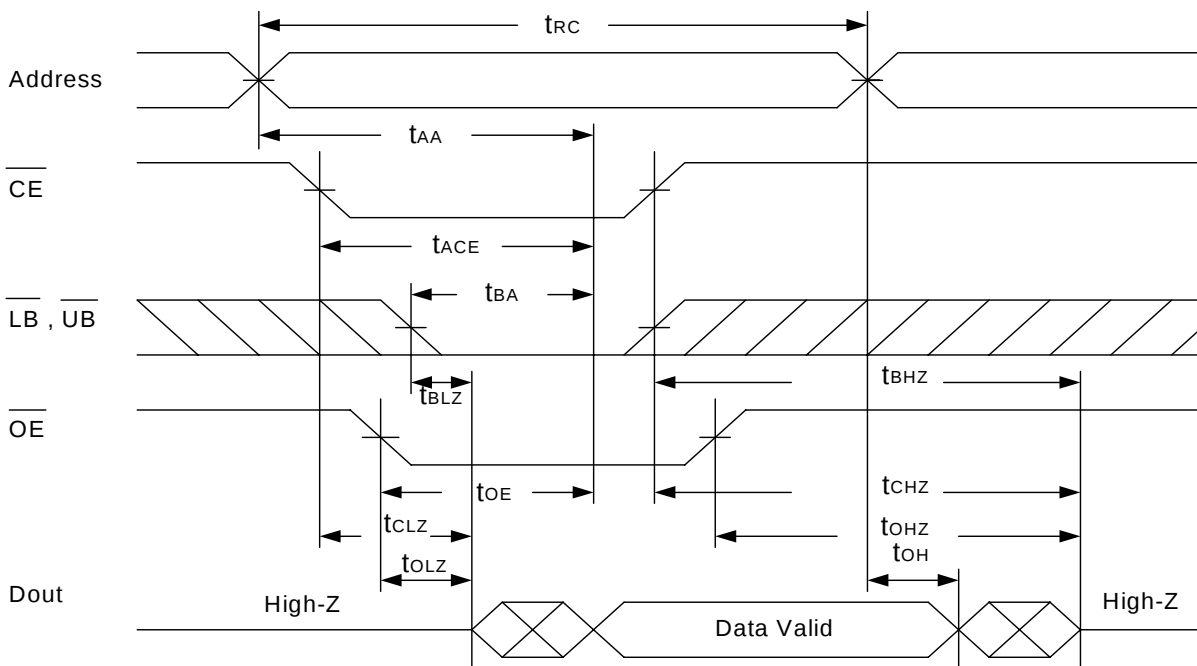


TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2)



READ CYCLE 2 ($\overline{CE}$ and $\overline{OE}$ Controlled) (1,3,4,5)



Notes :

1. $\overline{WE}$ is high for read cycle.
2. Device is continuously selected $\overline{OE}$ = low, $\overline{CE}$ = low, $\overline{LB}$ or $\overline{UB}$ = low.
3. Address must be valid prior to or coincident with $\overline{CE}$ = low, $\overline{LB}$ or $\overline{UB}$ = low transition; otherwise t_{AA} is the limiting parameter.
4. t_{CLZ} , t_{BLZ} , t_{OLZ} , t_{CHZ} , t_{BHZ} and t_{OHZ} are specified with C_L = 5pF. Transition is measured ± 500 mV from steady state.
5. At any given temperature and voltage condition, t_{CHZ} is less than t_{CLZ} , t_{BHZ} is less than t_{BLZ} , t_{OHZ} is less than t_{OLZ} .



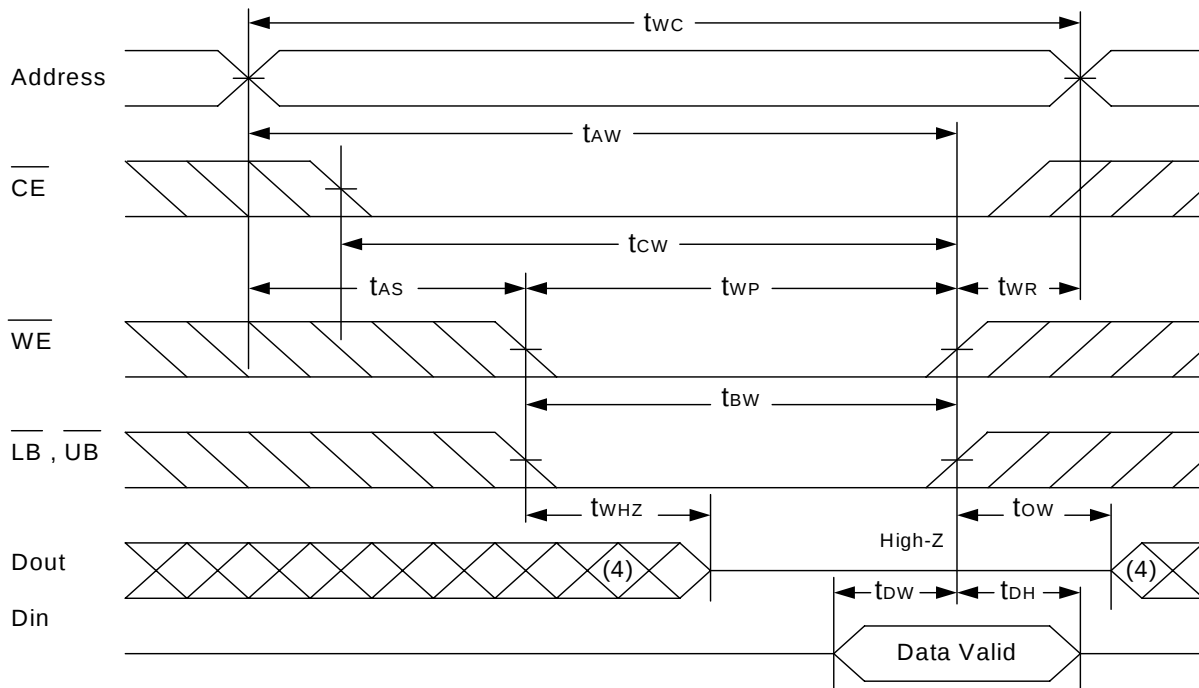
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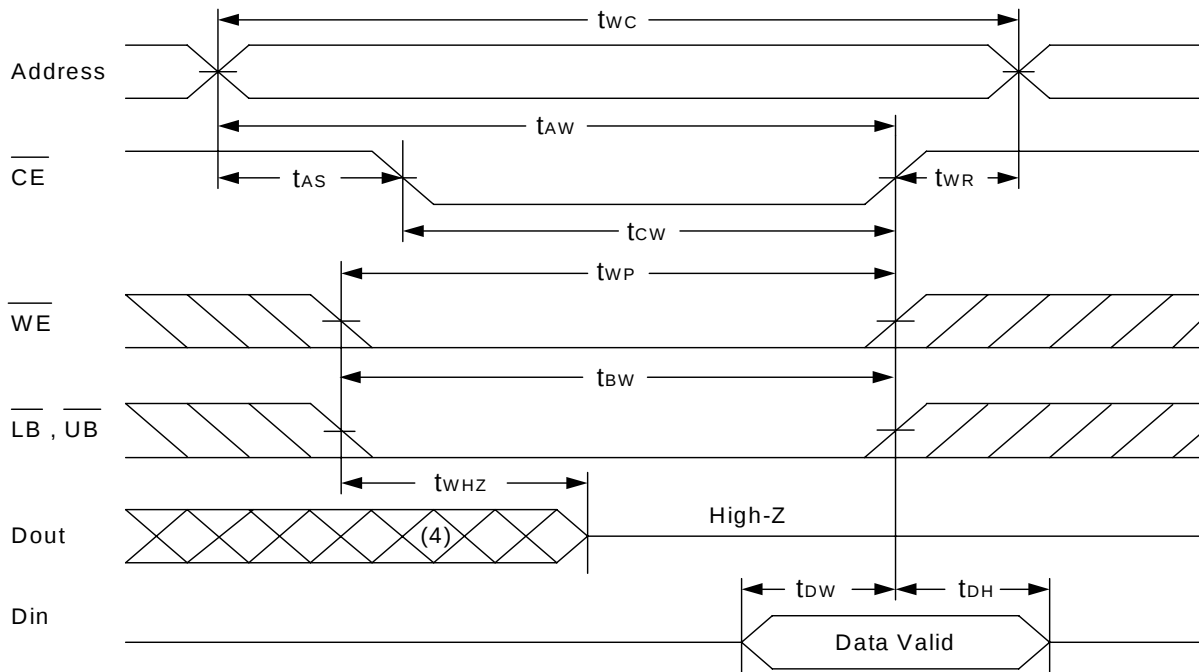
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WRITE CYCLE 1 ($\overline{WE}$ Controlled) (1,2,3,5,6)



WRITE CYCLE 2 ($\overline{CE}$ Controlled) (1,2,5,6)





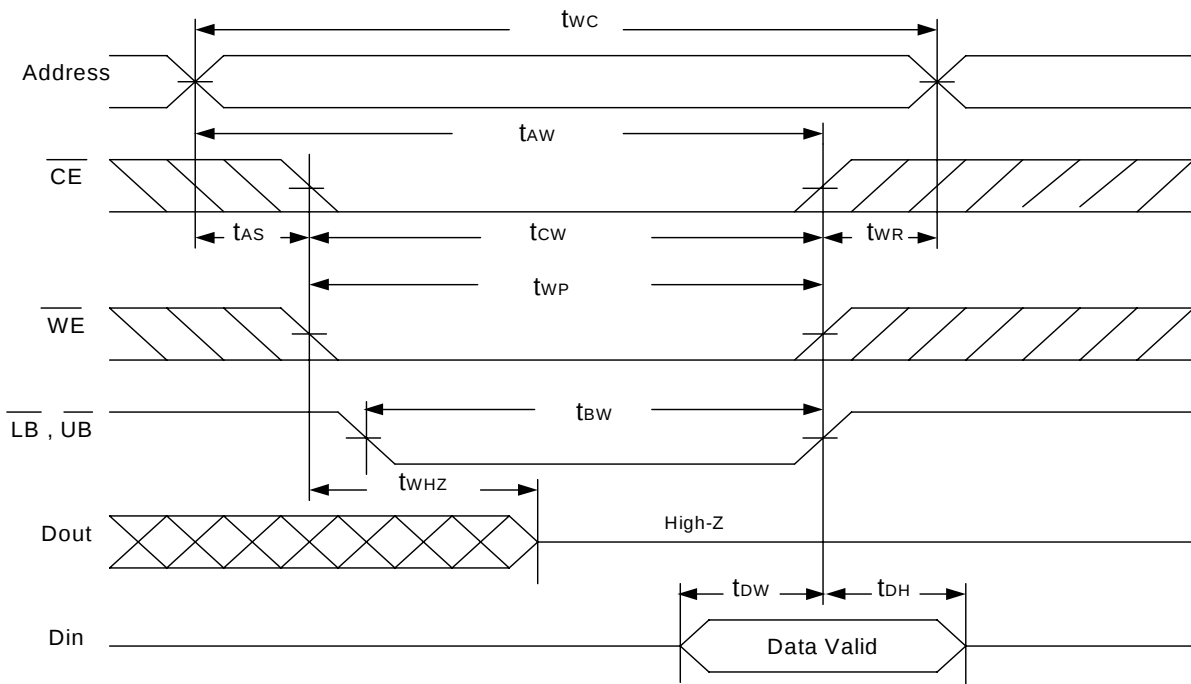
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WRITE CYCLE 3 ($\overline{\text{LB}}$, $\overline{\text{UB}}$ Controlled) (1,2,5,6)

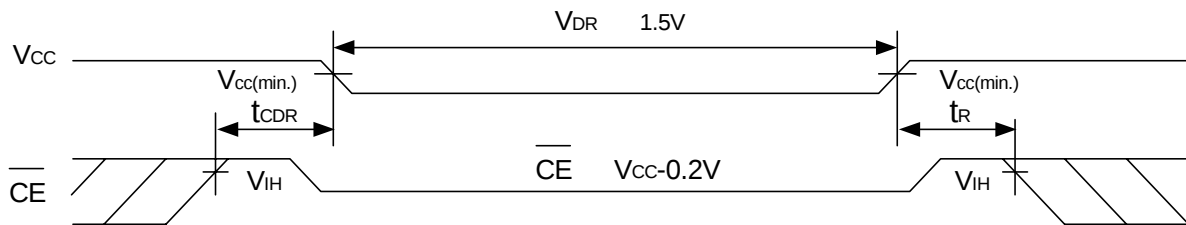
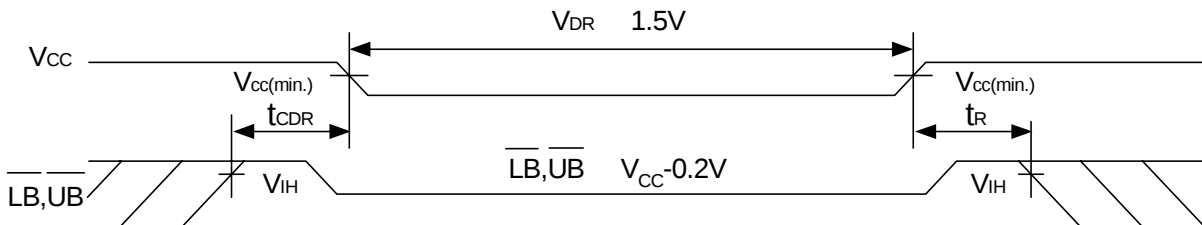


Notes :

1. $\overline{\text{WE}}$, $\overline{\text{CE}}$, $\overline{\text{LB}}$, $\overline{\text{UB}}$ must be high during all address transitions.
2. A write occurs during the overlap of a low $\overline{\text{CE}}$, low $\overline{\text{WE}}$, $\overline{\text{LB}}$ or $\overline{\text{UB}}$ = low.
3. During a $\overline{\text{WE}}$ controlled write cycle with $\overline{\text{OE}}$ low, t_{WP} must be greater than $t_{\text{WHZ}} + t_{\text{BW}}$ to allow the drivers to turn off and data to be placed on the bus.
4. During this period, I/O pins are in the output state, and input signals must not be applied.
5. If the $\overline{\text{CE}}$, $\overline{\text{LB}}$, $\overline{\text{UB}}$ low transition occurs simultaneously with or after $\overline{\text{WE}}$ low transition, the outputs remain in a high impedance state.
6. t_{OW} and t_{WHZ} are specified with $C_L = 5\text{pF}$. Transition is measured $\pm 500\text{mV}$ from steady state.

**DATA RETENTION CHARACTERISTICS** ($T_A = 0$ to 70 / -20 to 85 (E))

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Vcc for Data Retention	V_{DR}	$\overline{CE}$ $V_{CC}-0.2V$	1.5	-	3.6	V
Data Retention Current	I_{DR}	$V_{CC}=1.5V$ $\overline{CE}$ $V_{CC}-0.2V$	- L	1	50	μA
			- LL	0.5	20	μA
Chip Disable to Data Retention Time	t_{CDR}	See Data Retention Waveforms (below)	0	-	-	ms
Recovery Time	t_R		5	-	-	ms

DATA RETENTION WAVEFORM**Low Vcc Data Retention Waveform (1)** ($\overline{CE}$ controlled)**Low Vcc Data Retention Waveform (2)** ($\overline{LB}, \overline{UB}$ controlled)



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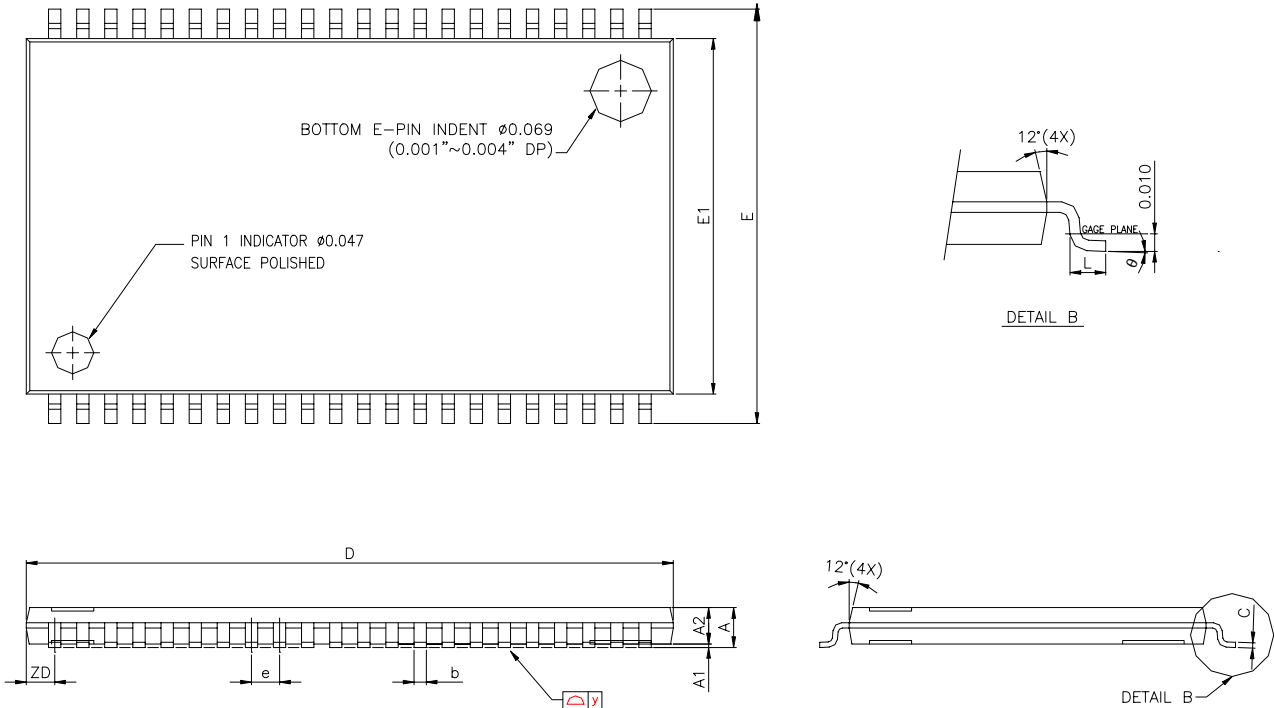
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PACKAGE OUTLINE DIMENSION

44-pin 400mil TSOP- Package Outline Dimension



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHS		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00	-	1.20	0.039	-	0.047
A1	0.05	-	0.15	0.002	-	0.006
A2	0.95	1.00	1.05	0.037	0.039	0.041
b	0.30	0.35	0.45	0.012	0.014	0.018
c	0.12	-	0.21	0.0047	-	0.083
D	18.313	18.415	18.517	0.721	0.725	0.728
E	11.854	11.836	11.838	0.460	0.466	0.470
E1	10.058	10.180	10.282	0.398	0.400	0.404
e	-	0.800	-	-	0.0315	-
L	0.40	0.50	0.60	0.0157	0.020	0.0236
2D	-	0.805	-	-	0.0317	-
y	0.00	-	0.076	0.000	-	0.003
Θ	0°	-	5°	0°	-	5°



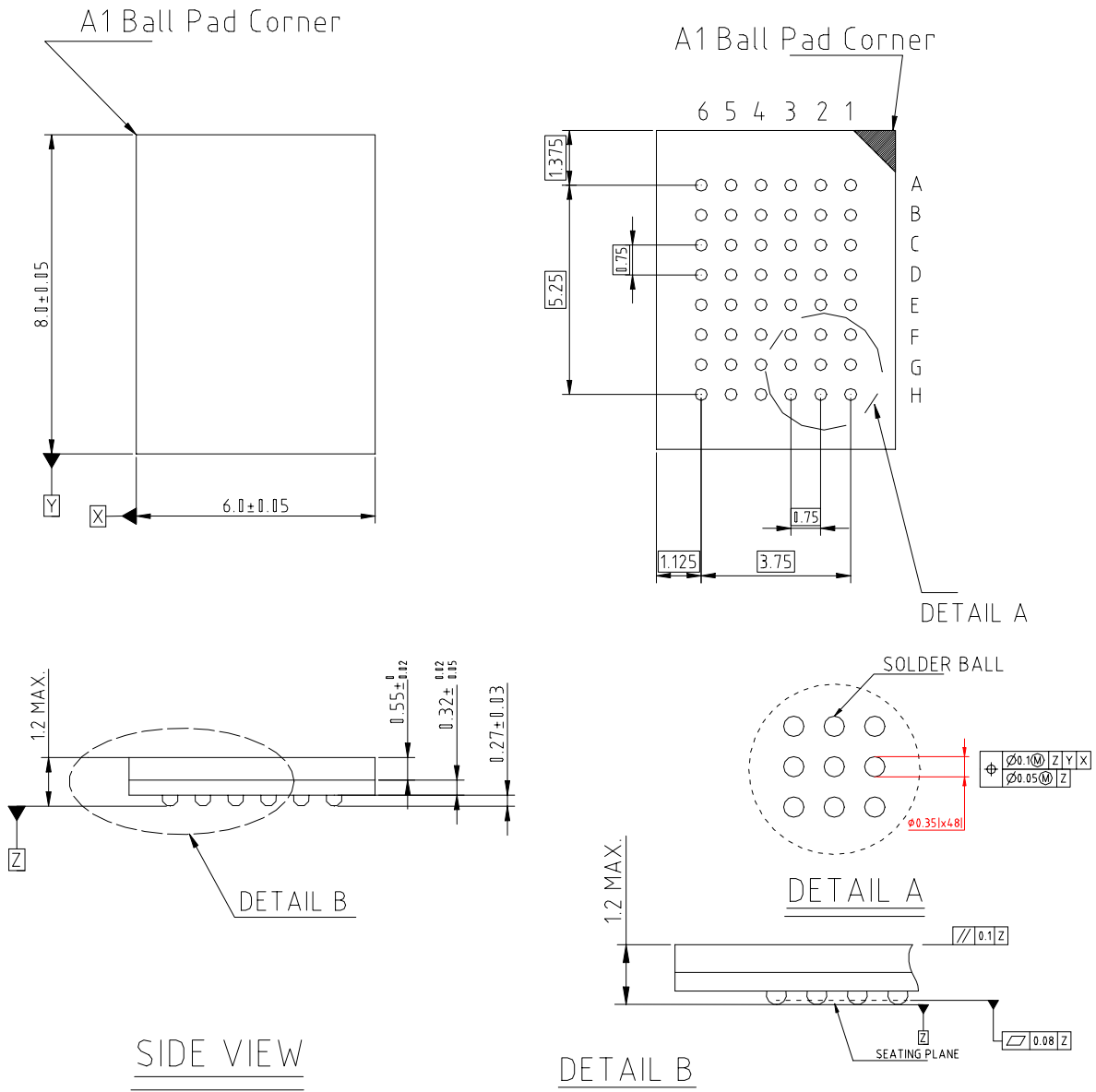
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48-pin 6mm × 8mm TFBGA Package Outline Dimension





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ORDERING INFORMATION**COMMERCIAL TEMPERATURE**

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μ A) TYP.	PACKAGE
UT62L12816MC-55L	55	20	44 PIN TSOP-
UT62L12816MC-55LL	55	2	44 PIN TSOP-
UT62L12816MC-70L	70	20	44 PIN TSOP-
UT62L12816MC-70LL	70	2	44 PIN TSOP-
UT62L12816MC-100L	100	20	44 PIN TSOP-
UT62L12816MC-100LL	100	2	44 PIN TSOP-
UT62L12816BS-55L	55	20	48 PIN TFBGA
UT62L12816BS-55LL	55	2	48 PIN TFBGA
UT62L12816BS-70L	70	20	48 PIN TFBGA
UT62L12816BS-70LL	70	2	48 PIN TFBGA
UT62L12816BS-100L	100	20	48 PIN TFBGA
UT62L12816BS-100LL	100	2	48 PIN TFBGA

EXTENDED TEMPERATURE

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μ A) TYP.	PACKAGE
UT62L12816MC-55LE	55	20	44 PIN TSOP-
UT62L12816MC-55LLE	55	2	44 PIN TSOP-
UT62L12816MC-70LE	70	20	44 PIN TSOP-
UT62L12816MC-70LLE	70	2	44 PIN TSOP-
UT62L12816MC-100LE	100	20	44 PIN TSOP-
UT62L12816MC-100LLE	100	2	44 PIN TSOP-
UT62L12816BS-55LE	55	20	48 PIN TFBGA
UT62L12816BS-55LLE	55	2	48 PIN TFBGA
UT62L12816BS-70LE	70	20	48 PIN TFBGA
UT62L12816BS-70LLE	70	2	48 PIN TFBGA
UT62L12816BS-100LE	100	20	48 PIN TFBGA
UT62L12816BS-100LLE	100	2	48 PIN TFBGA



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ORDERING INFORMATION (for lead free product)**COMMERCIAL TEMPERATURE**

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μ A) TYP.	PACKAGE
UT62L12816MCL-55L	55	20	44 PIN TSOP-
UT62L12816MCL-55LL	55	2	44 PIN TSOP-
UT62L12816MCL-70L	70	20	44 PIN TSOP-
UT62L12816MCL-70LL	70	2	44 PIN TSOP-
UT62L12816MCL-100L	100	20	44 PIN TSOP-
UT62L12816MCL-100LL	100	2	44 PIN TSOP-
UT62L12816BSL-55L	55	20	48 PIN TFBGA
UT62L12816BSL-55LL	55	2	48 PIN TFBGA
UT62L12816BSL-70L	70	20	48 PIN TFBGA
UT62L12816BSL-70LL	70	2	48 PIN TFBGA
UT62L12816BSL-100L	100	20	48 PIN TFBGA
UT62L12816BSL-100LL	100	2	48 PIN TFBGA

EXTENDED TEMPERATURE

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μ A) TYP.	PACKAGE
UT62L12816MCL-55LE	55	20	44 PIN TSOP-
UT62L12816MCL-55LLE	55	2	44 PIN TSOP-
UT62L12816MCL-70LE	70	20	44 PIN TSOP-
UT62L12816MCL-70LLE	70	2	44 PIN TSOP-
UT62L12816MCL-100LE	100	20	44 PIN TSOP-
UT62L12816MCL-100LLE	100	2	44 PIN TSOP-
UT62L12816BSL-55LE	55	20	48 PIN TFBGA
UT62L12816BSL-55LLE	55	2	48 PIN TFBGA
UT62L12816BSL-70LE	70	20	48 PIN TFBGA
UT62L12816BSL-70LLE	70	2	48 PIN TFBGA
UT62L12816BSL-100LE	100	20	48 PIN TFBGA
UT62L12816BSL-100LLE	100	2	48 PIN TFBGA



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